

IN THE CLAIMS

1.(Five times amended)

An integrated circuit comprising:

a dielectric layer formed over a substrate;

a first damascene structure in the dielectric layer, the first damascene structure comprising a bottom surface and first and second sidewalls;

a first conductor located in the damascene structure, the conductor comprising a conductive material;

a first liner layer lining the bottom surface and sidewalls of the first damascene structure and encapsulating the first conductor by contacting a top surface of the first conductor, the liner layer imparts a random grain orientation in the conductive material of the first conductor to improve electromigration lifetime of the first conductor;

a second damascene structure in the dielectric layer, the second damascene structure comprising a bottom surface and second sidewalls and disposed above said first damascene structure;

a second conductor located in the damascene structure, the conductor comprising a conductive material;

a second liner layer lining the bottom surface and sidewalls of the second damascene structure and encapsulating the second conductor by contacting a top surface of the second conductor, the liner layer imparts a random grain orientation in the conductive material of the second conductor to improve electromigration lifetime of the second conductor; and

wherein said second liner layer is in contact with said first liner layer.